Wafer-Scale Thermal ALD of Superconducting TiN: A Scalable Process with Room-Temperature Predictive Mapping

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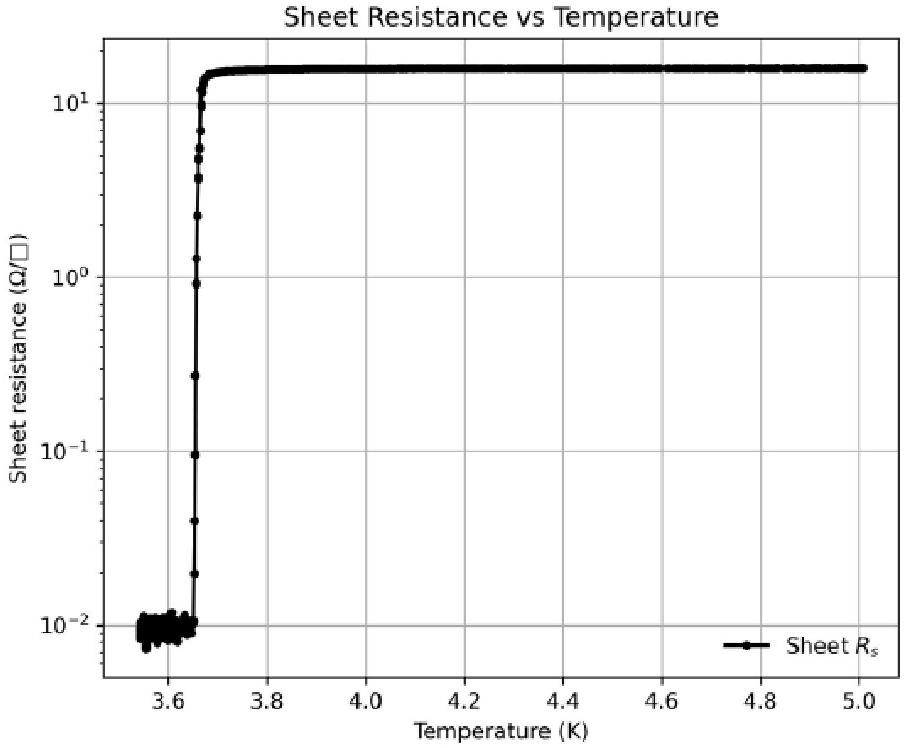

Figure 1. Cryogenic four-point probe measurement data for a TiN thin film deposited on a 200 mm Si-wafer using thermal batch ALD at 480°C, showing a Tc of 3.65 K.